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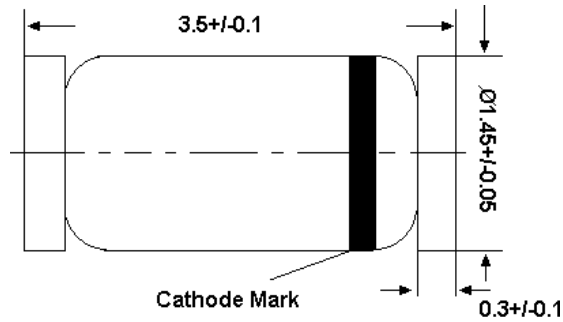
PLED

BZV55C2V0-MS THRU BZV55C75-MS

Product specification

Silicon Epitaxial Planar Zener Diodes

in MiniMELF case especially for automatic insertion. The Zener voltages are graded according to the international E24 standard. Smaller voltage tolerances and higher Zener voltages are upon request.



Glass case MiniMELF
Dimensions in mm

REEL SPECIFICATION

P/N	PKG	QTY
BZV55C2V0-MS THRU BZV55C75-MS	LL34	2500

Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Value	Unit
Power Dissipation	P _{tot}	500 ¹⁾	mW
Junction Temperature	T _j	175	°C
Storage Temperature Range	T _{stg}	- 55 to + 175	°C
¹⁾ Valid provided that electrodes are kept at ambient temperature			

Characteristics at Ta = 25°C

Thermal Resistance Junction to Ambient Air	R _{thA}	0.3 ¹⁾	K/mW
Forward Voltage at I _F = 100 mA	V _F	1	V
¹⁾ Valid provided that electrodes are kept at ambient temperature			

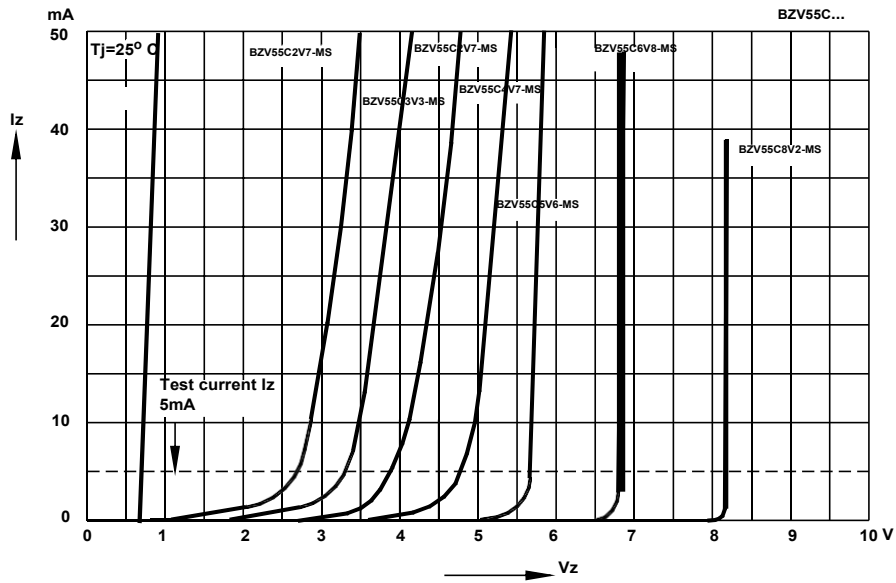
Characteristics at Ta = 25°C

P/N	Zener Voltage Range ¹⁾			Dynamic Resistance			Reverse Leakage Current			Temp. Coefficient of Zener Voltage
	V _{Zno} _m	V _{ZT}	at I _{ZT}	Z _{ZT}	Z _{ZK}	at I _{ZK}	T _a = 25°C	T _a = 125°C	at V _R	
	(V)	(V)	(mA)	Max. (Ω)	Max. (Ω)	(mA)	Max. (μA)	Max. (μA)	(V)	TKvz (%/K)
BZV55C2V0-MS	2.0	1.8...2.15	5	85	600	1	100	200	1	-0.09...-0.06
BZV55C2V2-MS	2.2	2.08...2.33	5	85	600	1	75	160	1	-0.09...-0.06
BZV55C2V4-MS	2.4	2.28...2.56	5	85	600	1	50	100	1	-0.09...-0.06
BZV55C2V7-MS	2.7	2.5...2.9	5	85	600	1	10	50	1	-0.09...-0.06
BZV55C3V0-MS	3.0	2.8...3.2	5	85	600	1	4	40	1	-0.08...-0.05
BZV55C3V3-MS	3.3	3.1...3.5	5	85	600	1	2	40	1	-0.08...-0.05
BZV55C3V6-MS	3.6	3.4...3.8	5	85	600	1	2	40	1	-0.08...-0.05
BZV55C3V9-MS	3.9	3.7...4.1	5	85	600	1	2	40	1	-0.08...-0.05
BZV55C4V3-MS	4.3	4...4.6	5	75	600	1	1	20	1	-0.06...-0.03
BZV55C4V7-MS	4.7	4.4...5	5	60	600	1	0.5	10	1	-0.05...+0.02
BZV55C5V1-MS	5.1	4.8...5.4	5	35	550	1	0.1	2	1	-0.02...+0.02
BZV55C5V6-MS	5.6	5.2...6	5	25	450	1	0.1	2	1	-0.05...+0.05
BZV55C6V2-MS	6.2	5.8...6.6	5	10	200	1	0.1	2	2	0.03...0.06
BZV55C6V8-MS	6.8	6.4...7.2	5	8	150	1	0.1	2	3	0.03...0.07
BZV55C7V5-MS	7.5	7...7.9	5	7	50	1	0.1	2	5	0.03...0.07
BZV55C8V2-MS	8.2	7.7...8.7	5	7	50	1	0.1	2	6.2	0.03...0.08
BZV55C9V1-MS	9.1	8.5...9.6	5	10	50	1	0.1	2	6.8	0.03...0.09
BZV55C10-MS	10	9.4...10.6	5	15	70	1	0.1	2	7.5	0.03...0.1
BZV55C11-MS	11	10.4...11.6	5	20	70	1	0.1	2	8.2	0.03...0.11
BZV55C12-MS	12	11.4...12.7	5	20	90	1	0.1	2	9.1	0.03...0.11
BZV55C13-MS	13	12.4...14.1	5	26	110	1	0.1	2	10	0.03...0.11
BZV55C15-MS	15	13.8...15.6	5	30	110	1	0.1	2	11	0.03...0.11
BZV55C16-MS	16	15.3...17.1	5	40	170	1	0.1	2	12	0.03...0.11
BZV55C18-MS	18	16.8...19.1	5	50	170	1	0.1	2	13	0.03...0.11
BZV55C20-MS	20	18.8...21.2	5	55	220	1	0.1	2	15	0.03...0.11
BZV55C22-MS	22	20.8...23.3	5	55	220	1	0.1	2	16	0.04...0.12
BZV55C24-MS	24	22.8...25.6	5	80	220	1	0.1	2	18	0.04...0.12
BZV55C27-MS	27	25.1...28.9	5	80	220	1	0.1	2	20	0.04...0.12
BZV55C30-MS	30	28...32	5	80	220	1	0.1	2	22	0.04...0.12
BZV55C33-MS	33	31...35	5	80	220	1	0.1	2	24	0.04...0.12
BZV55C36-MS	36	34...38	5	80	220	1	0.1	2	27	0.04...0.12
BZV55C39-MS	39	37...41	2.5	90	500	0.5	0.1	5	30	0.04...0.12
BZV55C43-MS	43	40...46	2.5	90	500	0.5	0.1	5	33	0.04...0.12
BZV55C47-MS	47	44...50	2.5	110	600	0.5	0.1	5	36	0.04...0.12
BZV55C51-MS	51	48...54	2.5	125	700	0.5	0.1	10	39	0.04...0.12
BZV55C56-MS	56	52...60	2.5	135	700	0.5	0.1	10	43	0.04...0.12
BZV55C62-MS	62	58...66	2.5	150	1000	0.5	0.1	10	47	0.04...0.12
BZV55C68-MS	68	64...72	2.5	200	1000	0.5	0.1	10	51	0.04...0.12
BZV55C75-MS	75	70...79	2.5	250	1000	0.5	0.1	10	56	0.04...0.12

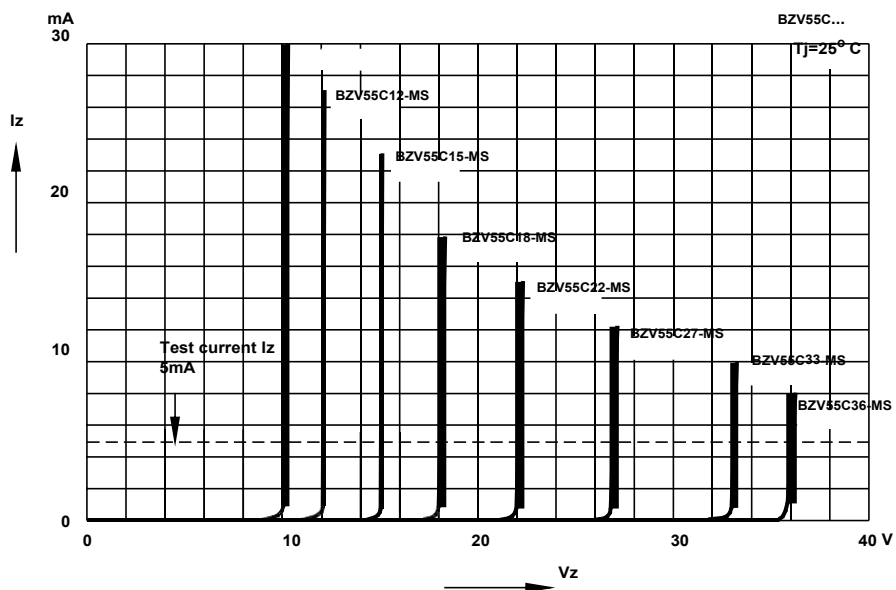
1) Tested with pulses t_p = 20 ms.

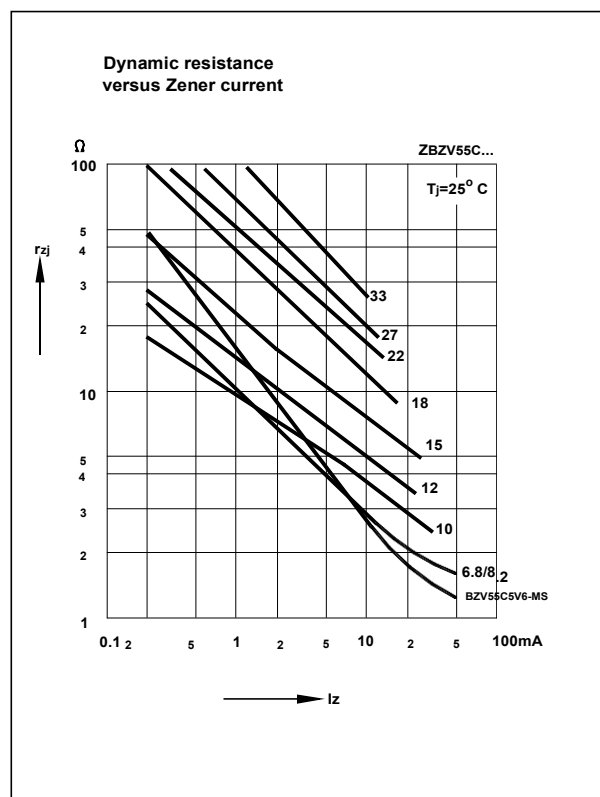
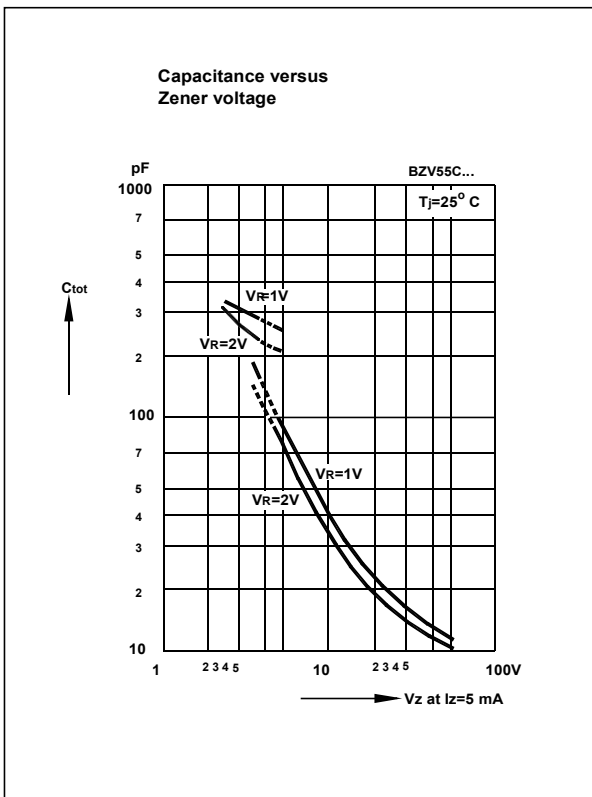
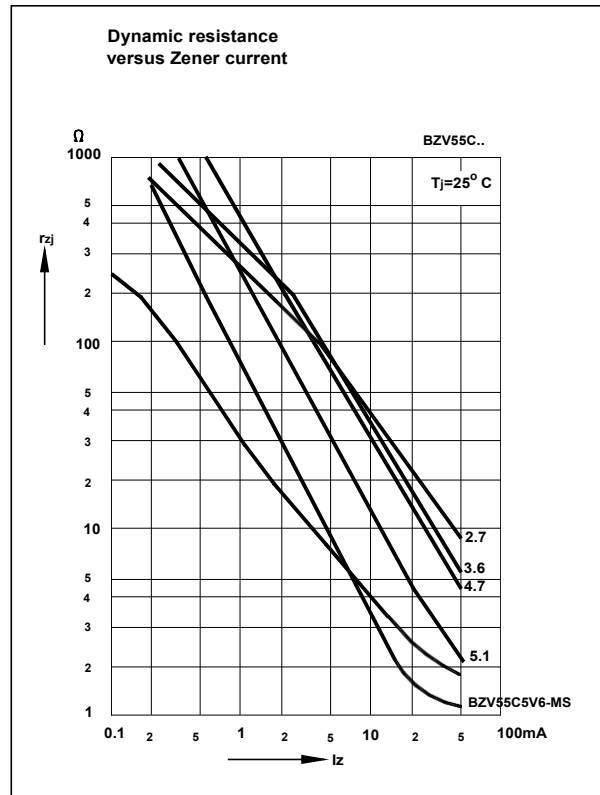
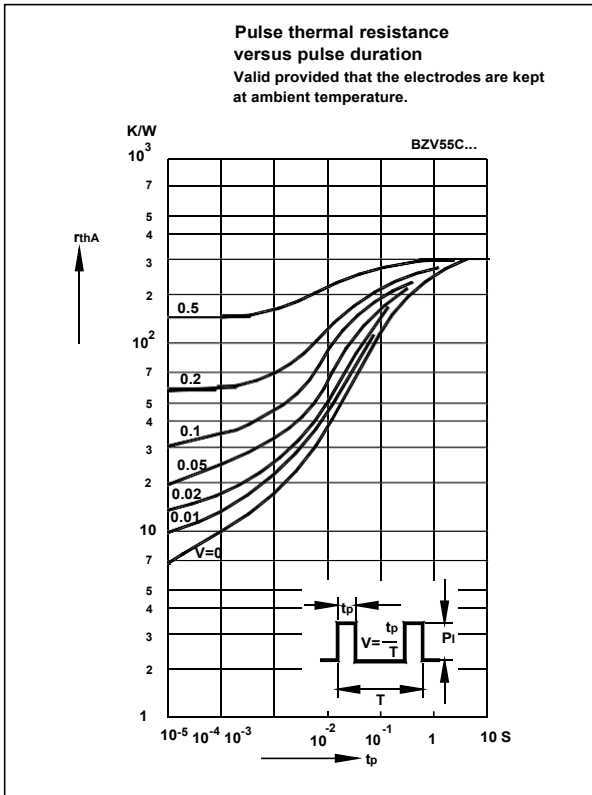
2) The BZV55C is a silicon diode with operation in forward direction. Hence, the index of all parameters should be "F" instead of "Z". Connect the cathode electrode to the negative pole.

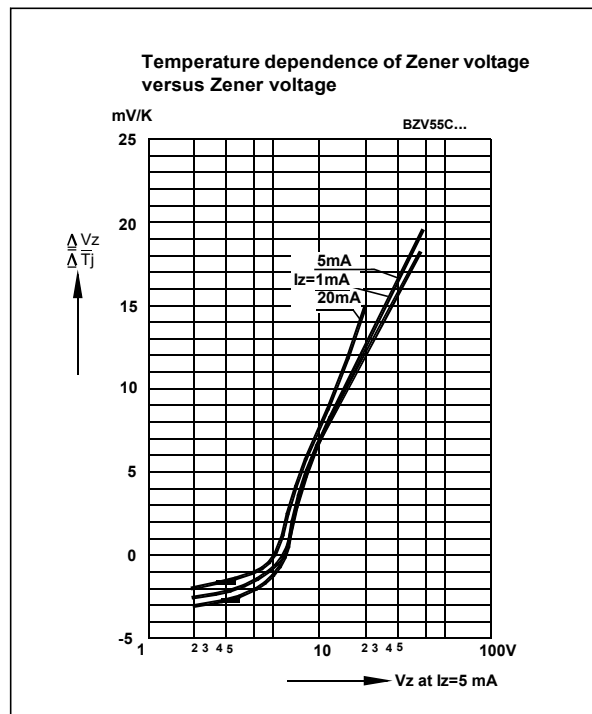
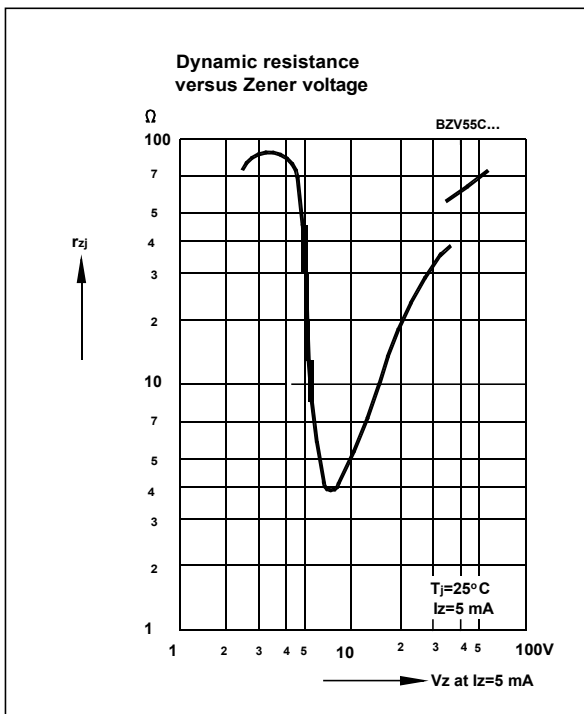
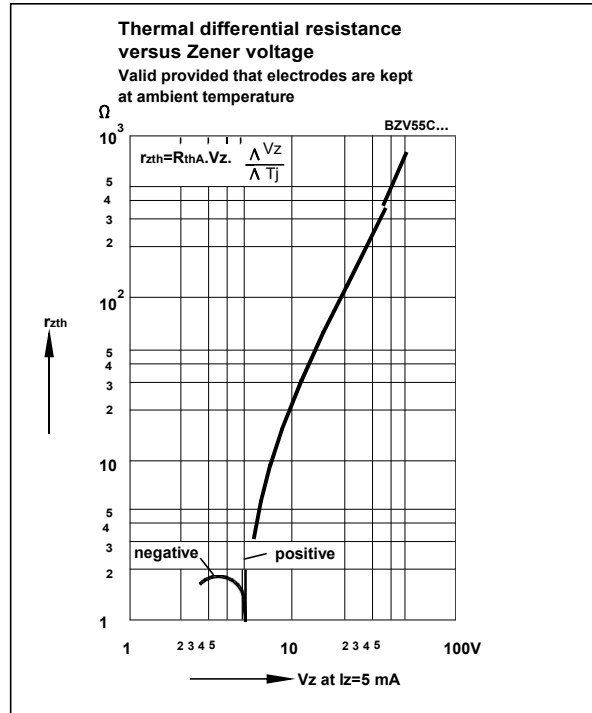
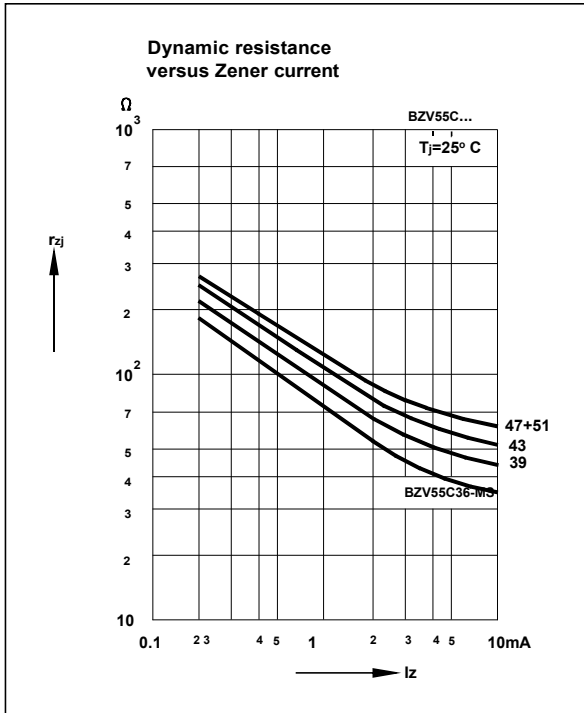
Breakdown characteristics
T_j = constant (pulsed)

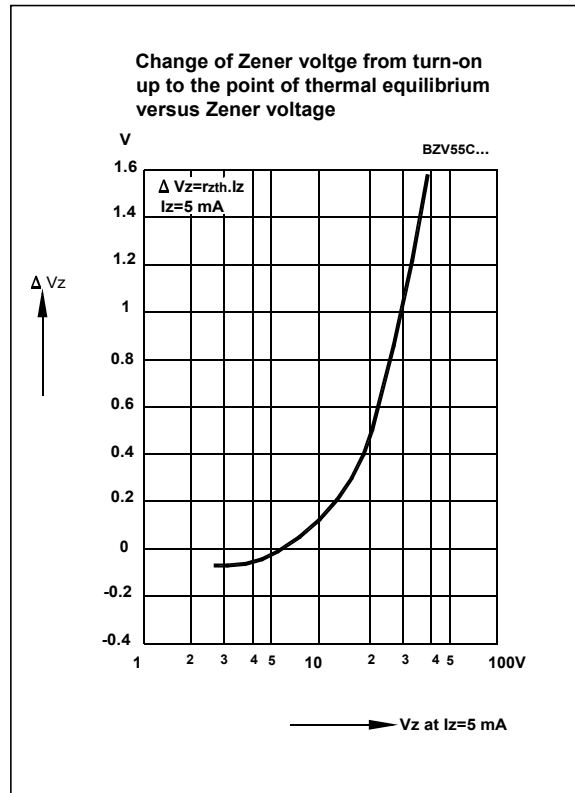
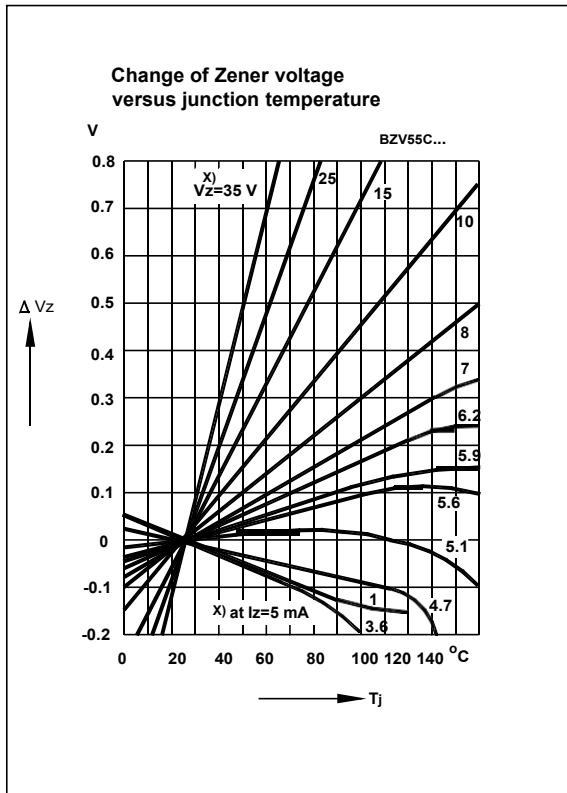
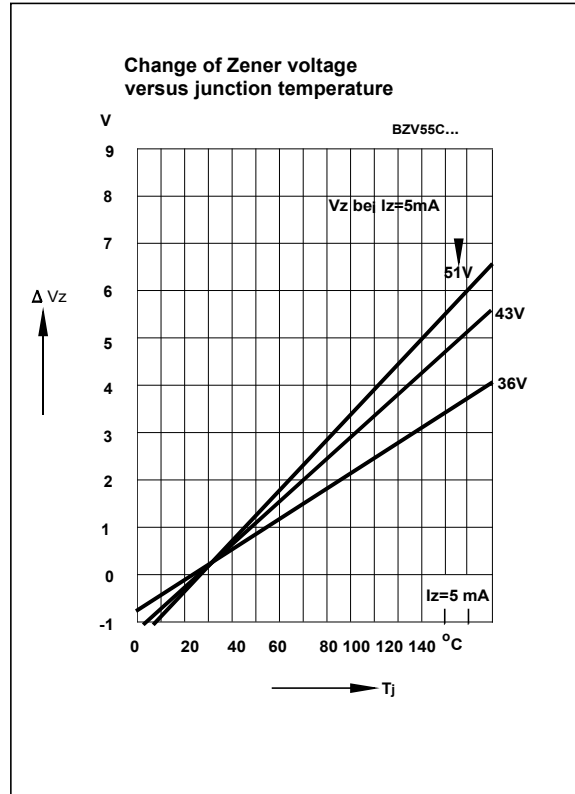
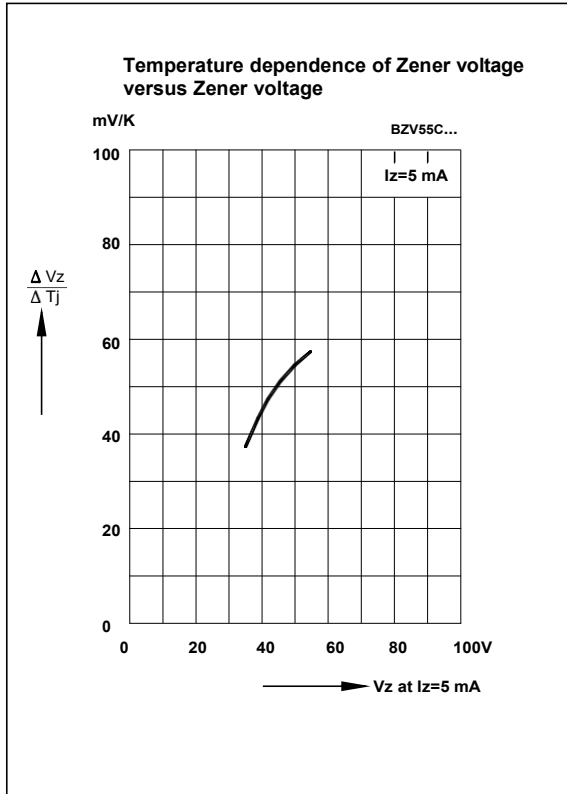


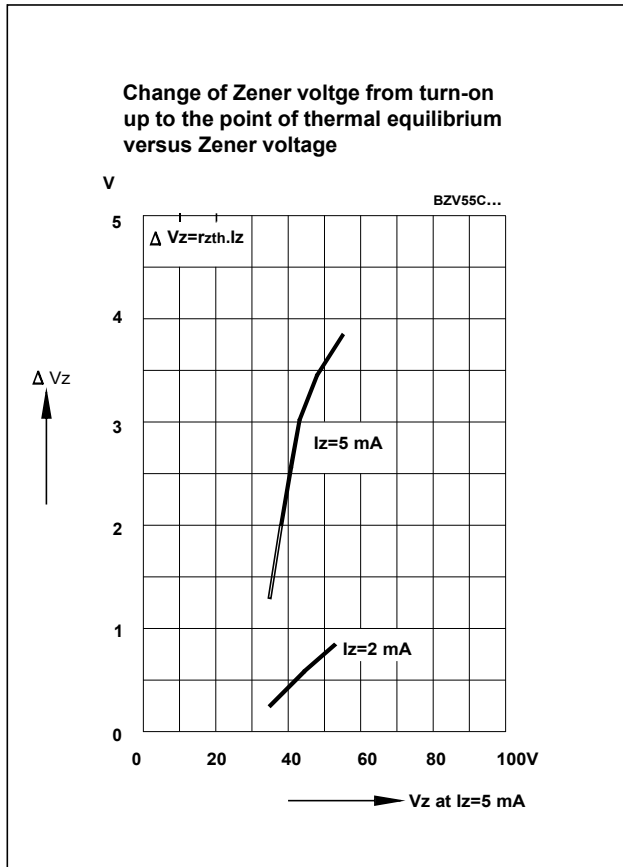
Breakdown characteristics
T_j = constant (pulsed)











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